Lecture 4: Heterojunction Bipolar Transistors (HBTs)

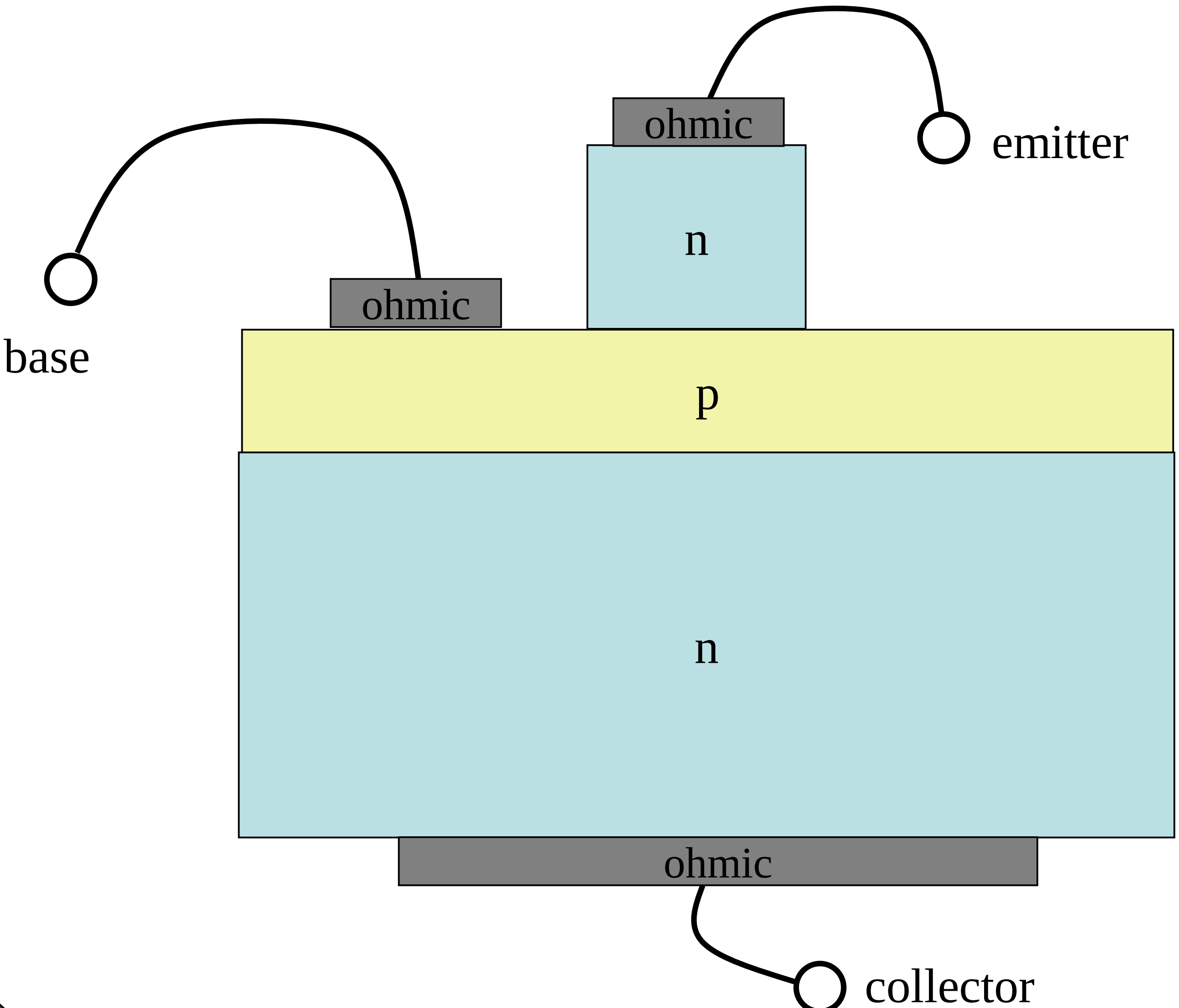
Bipolar means both electrons, holes participate in the device.

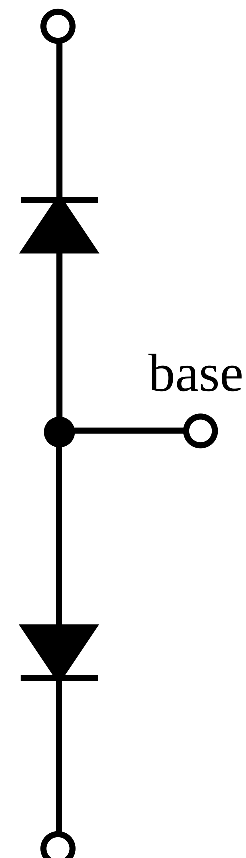
(In contrast, FET is unipolar.)

Outline for today

- n-p-n homojunction band diagrams
- n-p-n DC I-V curves, etc.
- DC circuit models
- Why are we doing this? YOU, the designer will need to know how different transistor geometries translate into different effective circuit elements.

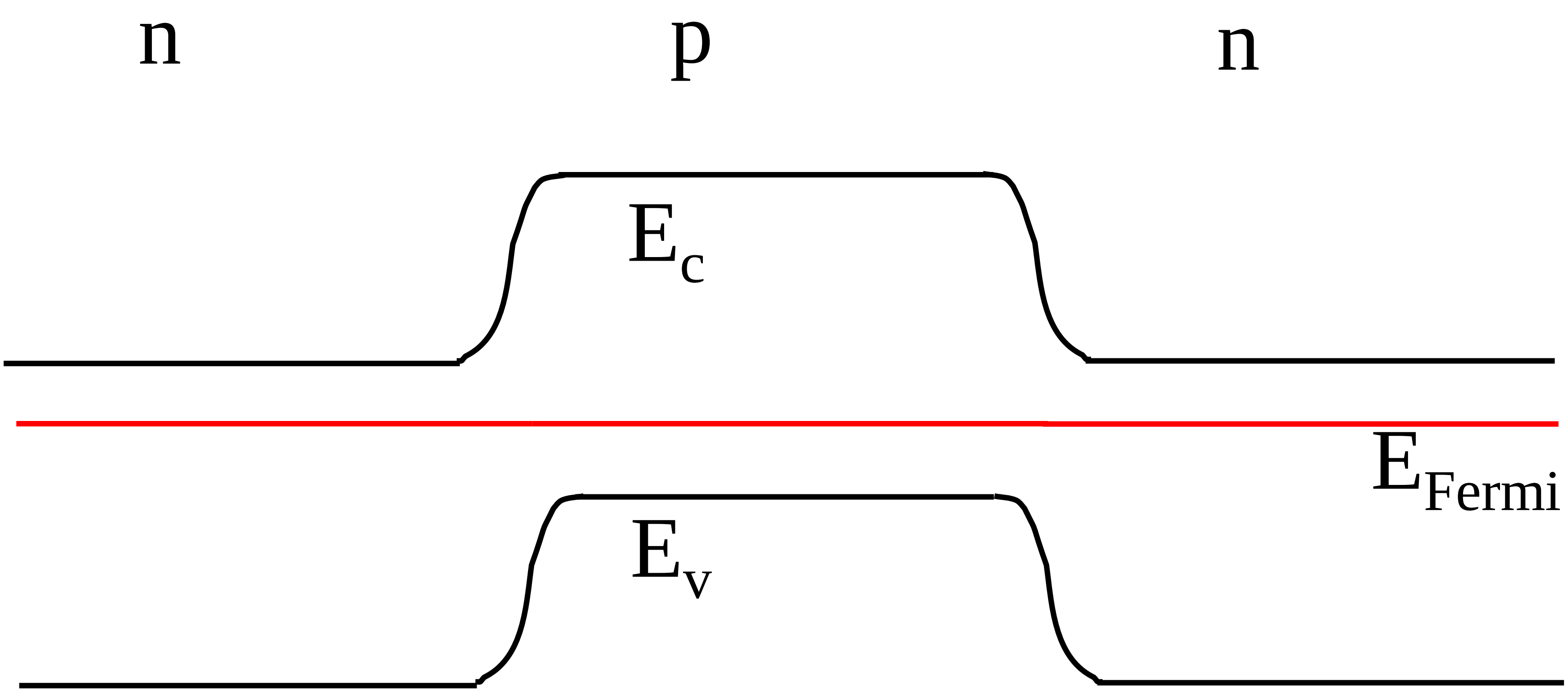
n-p-n geometry





circuit only
if base LONG

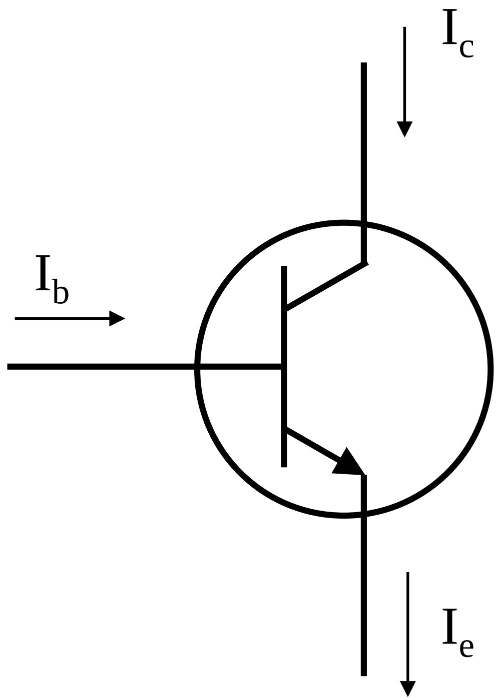
n-p-n junction at zero bias



Bias conditions

Mode	E-B	C-B
Normal active	forward	reverse
saturation	forward	forward
cutoff	reverse	reverse

“Normal active” bias



- E-B forward bias (V_b>V_e)
- C-B reverse bias (V_c>V_b)
- $I_{ce} = 100\ I_{be} = \beta I_{be}$

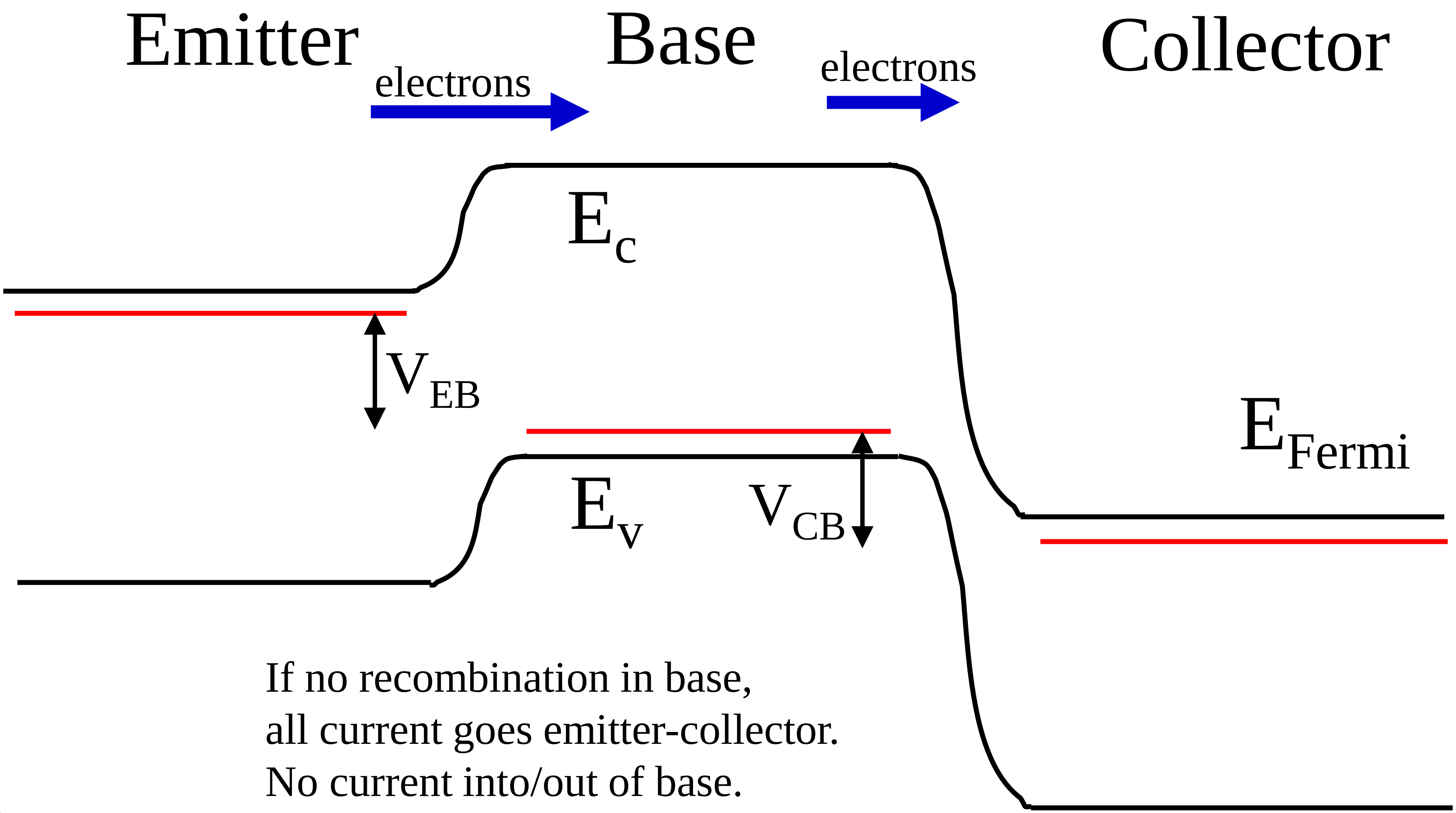
All of chapter 3 is about calculating β.

Many current components

- Electron drift E-B
- Electron diffusion E-B
- Hole drift E-B
- Hole diffusion E-B
- Electron drift C-B
- Electron diffusion C-B
- Hole drift C-B
- Hole diffusion C-B

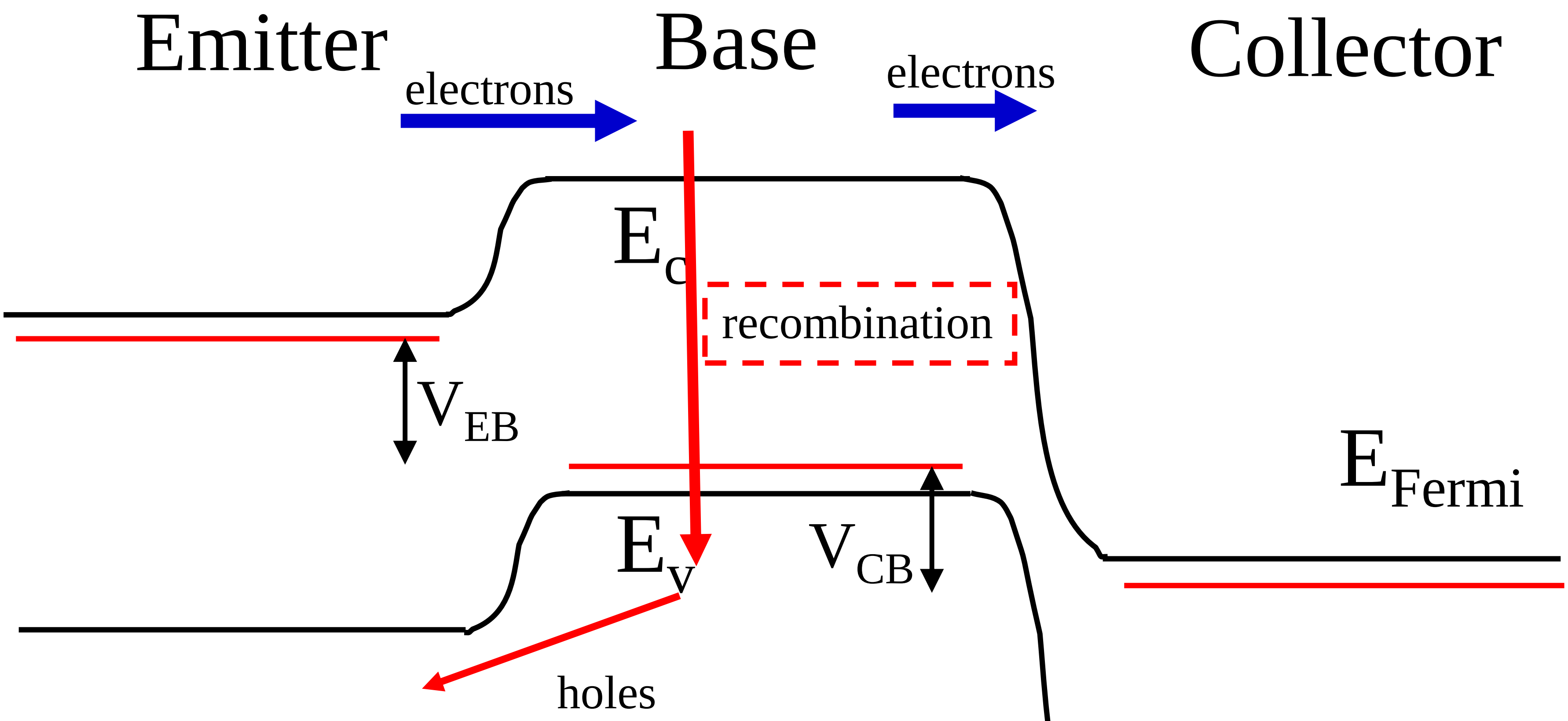
concentrate on these components, since they are the largest (Discuss why others small.)

"Normal active" band diagram



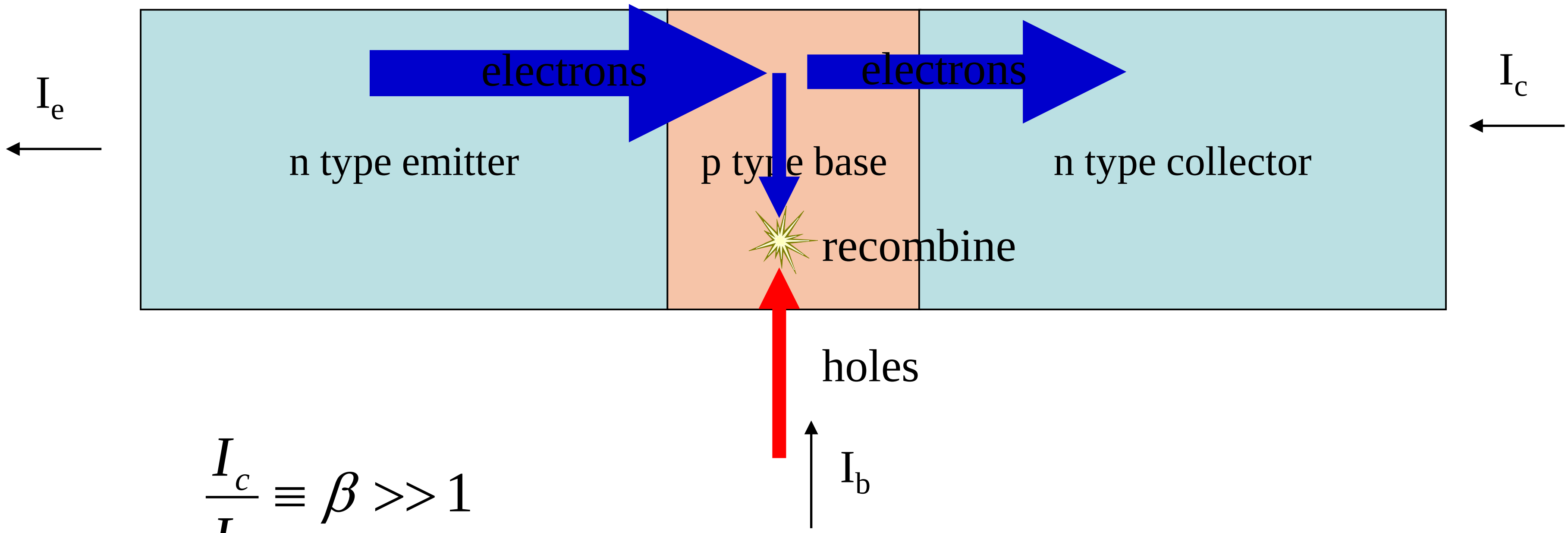
If no recombination in base,
all current goes emitter-collector.
No current into/out of base.

"Normal active" band diagram



- What fraction of electrons makes it, and what fraction recombines?
- Want W< L_n (diffusion length)
- Holes from B-E cause base current.

"Normal active" schematic

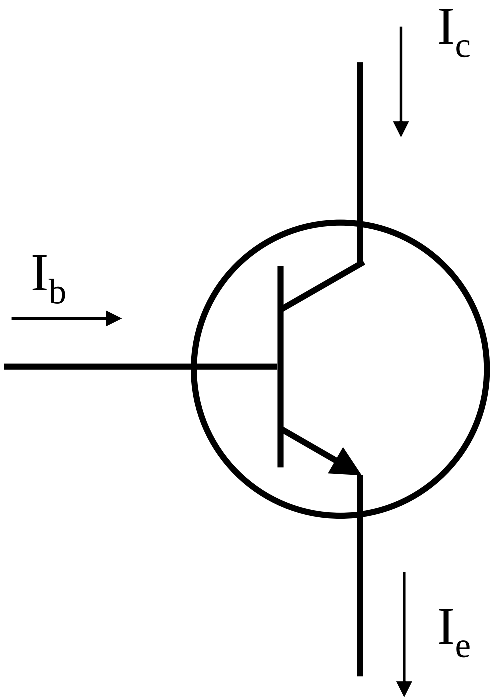


$$\frac{I_c}{I_b} \equiv \beta >> 1$$

$$\frac{I_c}{I_b} \approx \frac{\tau_n}{\tau_t}$$

$\tau_t \equiv$ transit time (discuss druken man analogy)

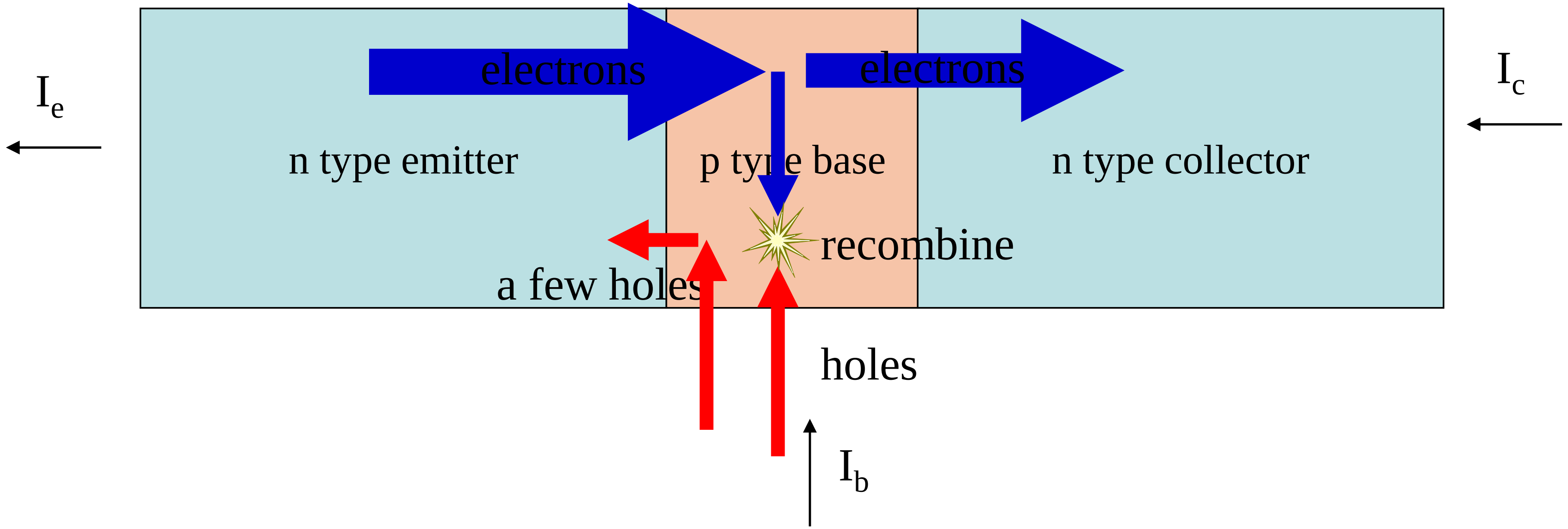
"Normal active" current gain



$$\frac{I_c}{I_b} \equiv \beta >> 1$$

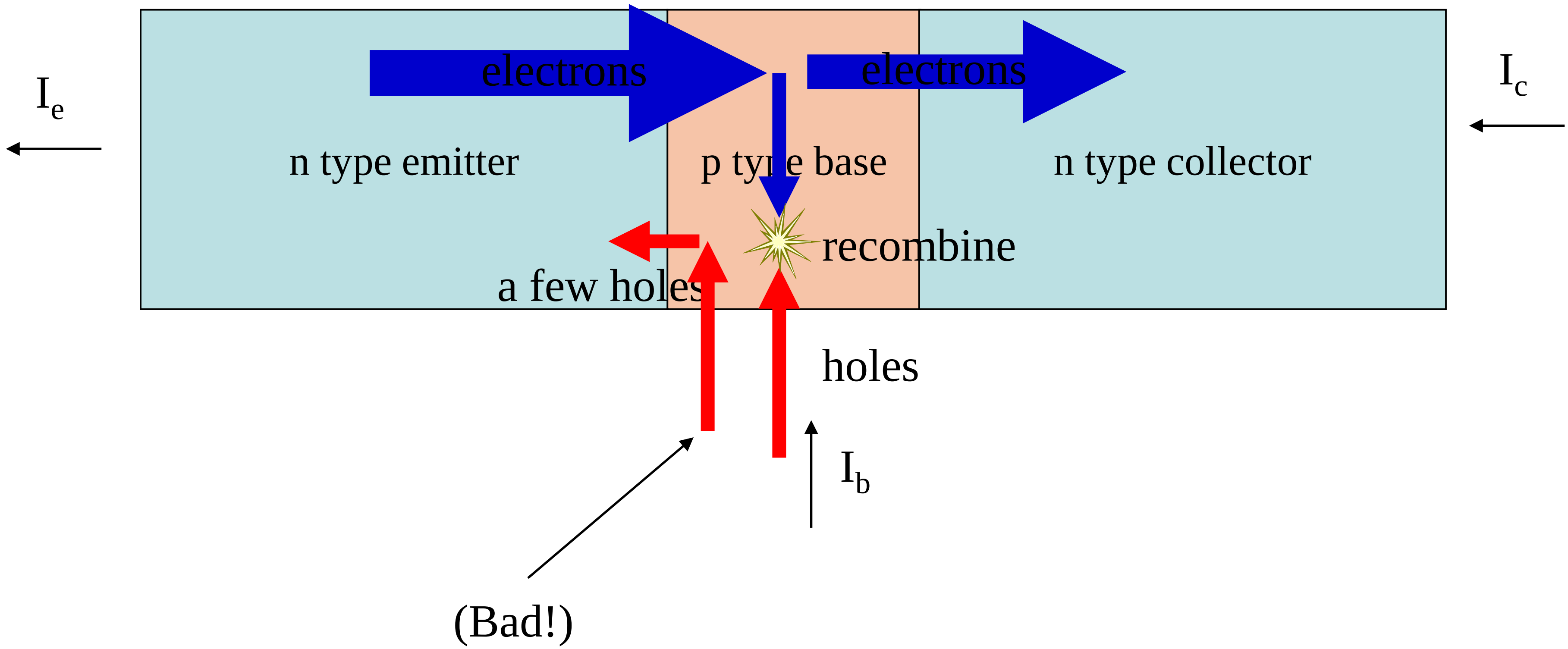
That is simplest circuit model. It just gets more complicated from here!

“Normal active” schematic



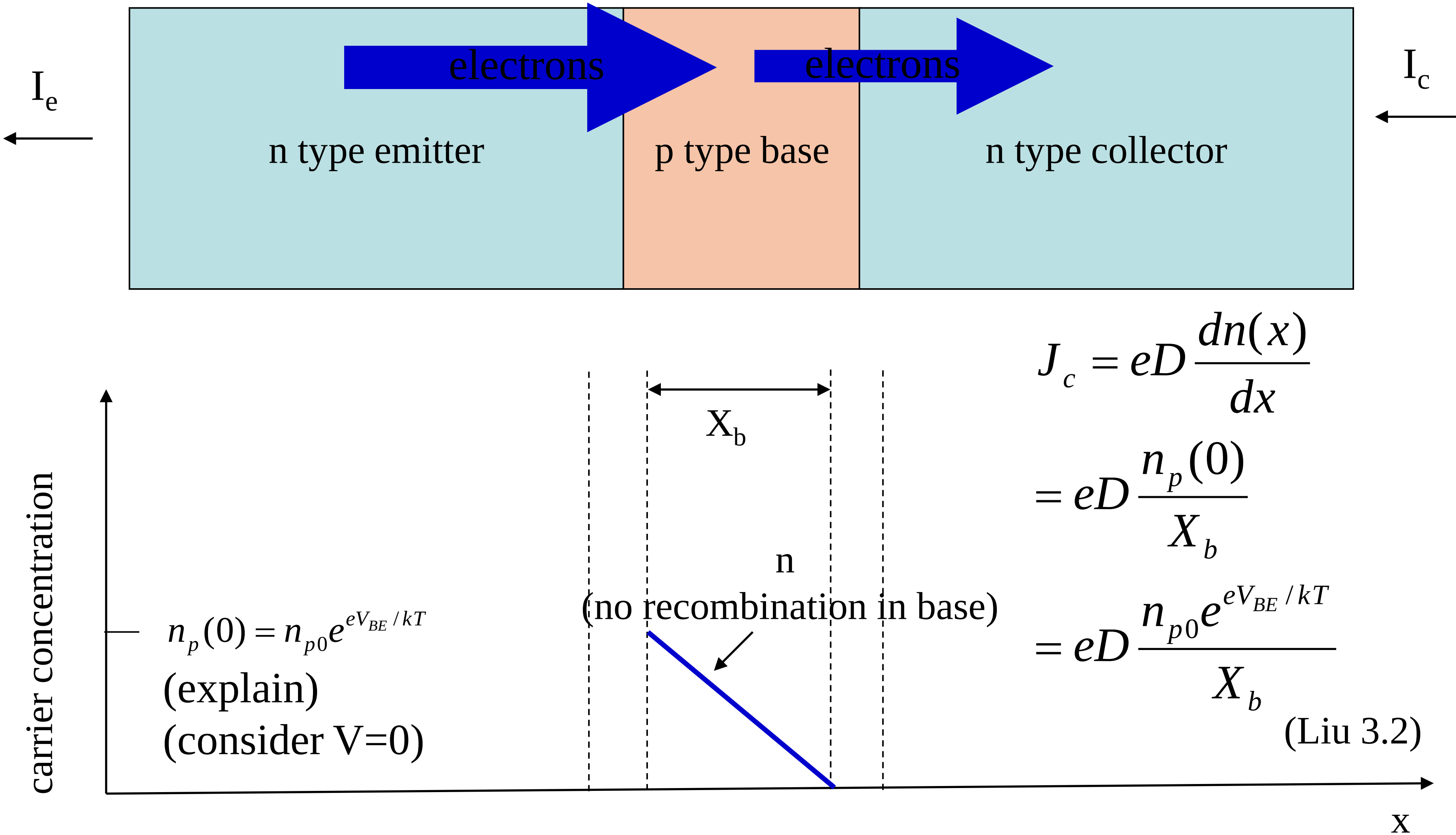
Goal: Find relationship between I_b, I_c

“Normal active” schematic



- Want low p-type doping.
- Can show need n>p
- But n>p bad for base resistance (speed)
- Solution later: heterojunctions block p injection into emitter
- HBTs can have p>n good for speed

"Normal active" schematic



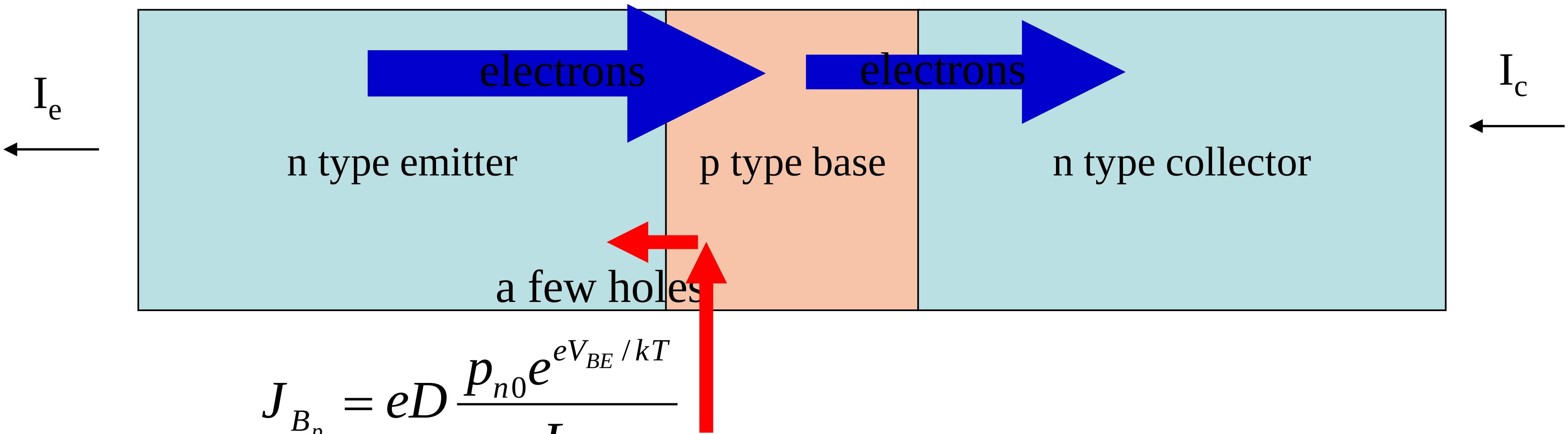
$n_p(0) = n_{p0} e^{eV_{BE}/kT}$
(explain)
(consider V=0)

$$J_c = eD \frac{dn(x)}{dx} = eD \frac{n_p(0)}{X_b} = eD \frac{n_{p0} e^{eV_{BE}/kT}}{X_b}$$

(Liu 3.2)

Discuss J vs. I. Discuss line vs. tanh.

"Normal active" schematic



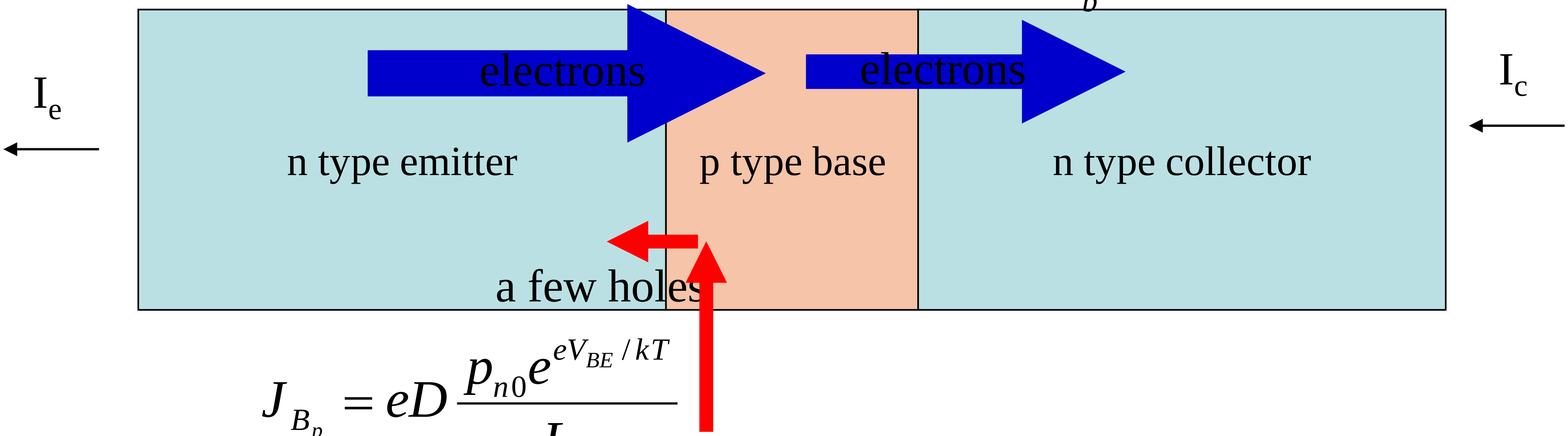
$$J_{B_p} = eD\frac{p_{n0}e^{eV_{BE}/kT}}{L_p}$$

(explain like HW#1)

Liu equation 3.1

"Normal active" schematic

$$J_c = eD\frac{n_{p0}e^{eV_{BE}/kT}}{X_b}$$



$$J_{B_p} = eD\frac{p_{n0}e^{eV_{BE}/kT}}{L_p}$$

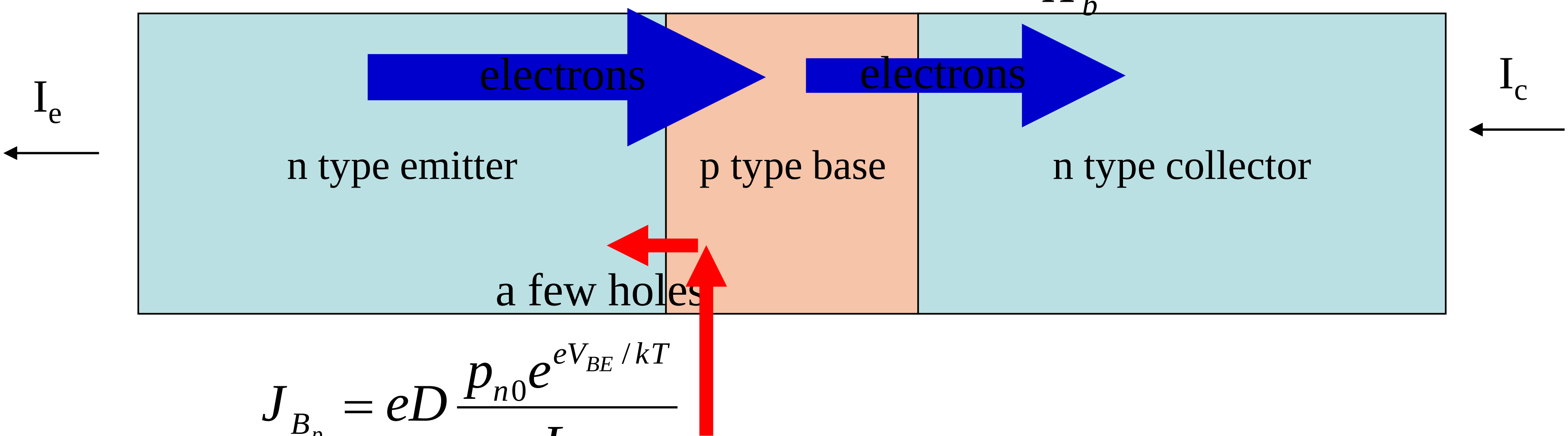
$$\frac{I_c}{I_b} \equiv \beta = \frac{eD\dfrac{n_{p0}e^{eV_{BE}/kT}}{X_b}}{eD\dfrac{p_{n0}e^{eV_{BE}/kT}}{L_p}} = \frac{\dfrac{n_{p0}}{X_b}}{\dfrac{p_{n0}}{L_p}} = \frac{n_{p0}}{p_{n0}}\frac{L_p}{X_b} ??? >> 1$$

$$Need \quad n_{p0} >> p_{n0}$$

Bad for base resistance. Bad for E-B capacitance. So bad for speed.

“Normal active” HBT

$$J_c = eD\frac{n_{p0}e^{eV_{BE}/kT}}{X_b}$$



$$J_{B_p} = eD\frac{p_{n0}e^{eV_{BE}/kT}}{L_p}$$

Holes exponentially suppressed if emitter is wider gap. (Graded.)

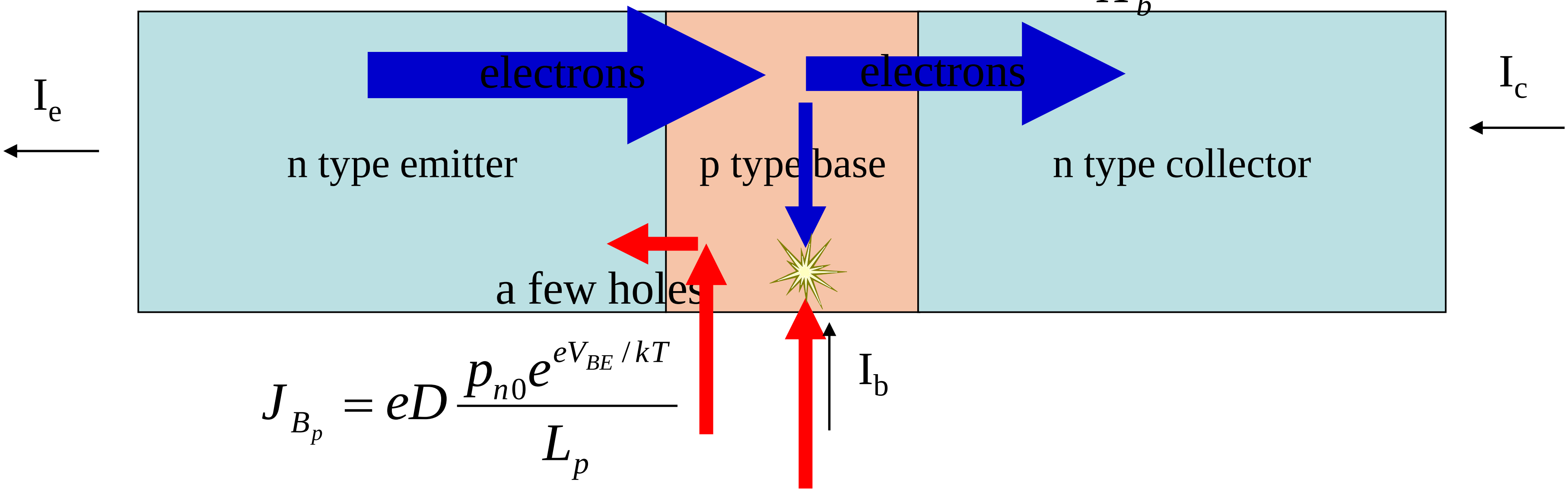
$$\frac{I_c}{I_b} \equiv \frac{n_{p0}}{p_{n0}}\frac{L_p}{X_b}e^{\Delta E_g/kT} >> 1$$

$$Don't\ \text{need}\ \ n_{p0} >> p_{n0}$$

Good for speed. Claims of 1 THz f_T in literature.

"Normal active" schematic

$$J_c = eD\frac{n_{p0}e^{eV_{BE}/kT}}{X_b}$$



$$J_{B_p} = eD\frac{p_{n0}e^{eV_{BE}/kT}}{L_p}$$

?

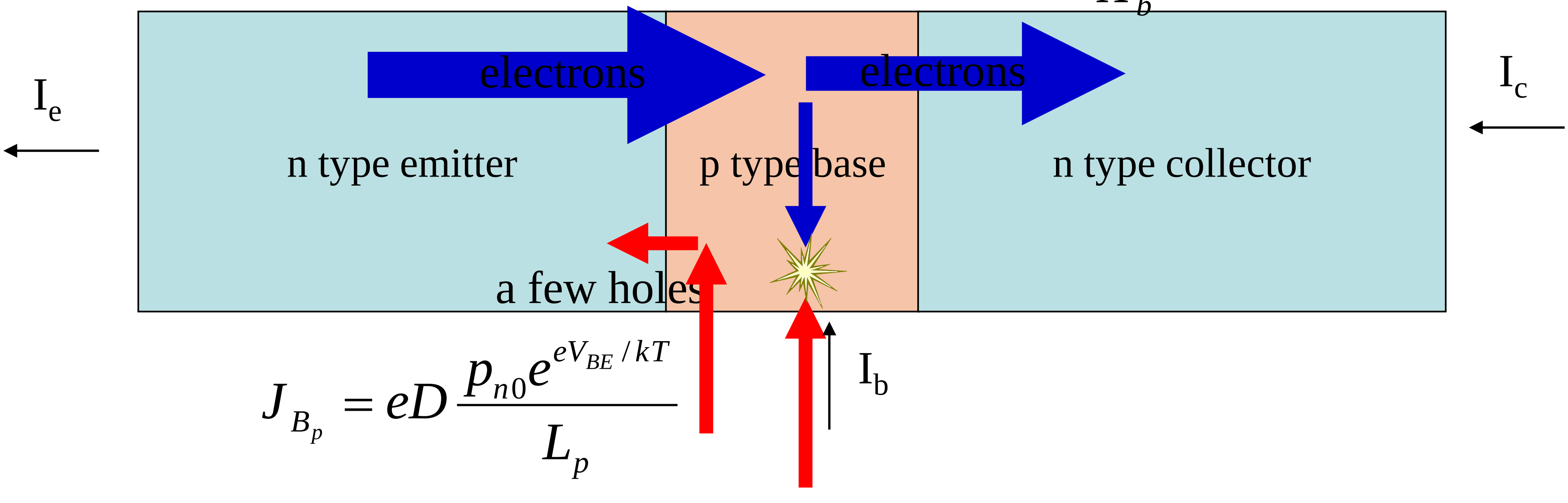
Depends on recombination processes in:

1. Surface (not contact)
2. Surface (at base contact)
3. Bulk
4. Space charge region

Try to minimize 1,2,4.

“Normal active” schematic

$$J_c = eD\frac{n_{p0}e^{eV_{BE}/kT}}{X_b}$$

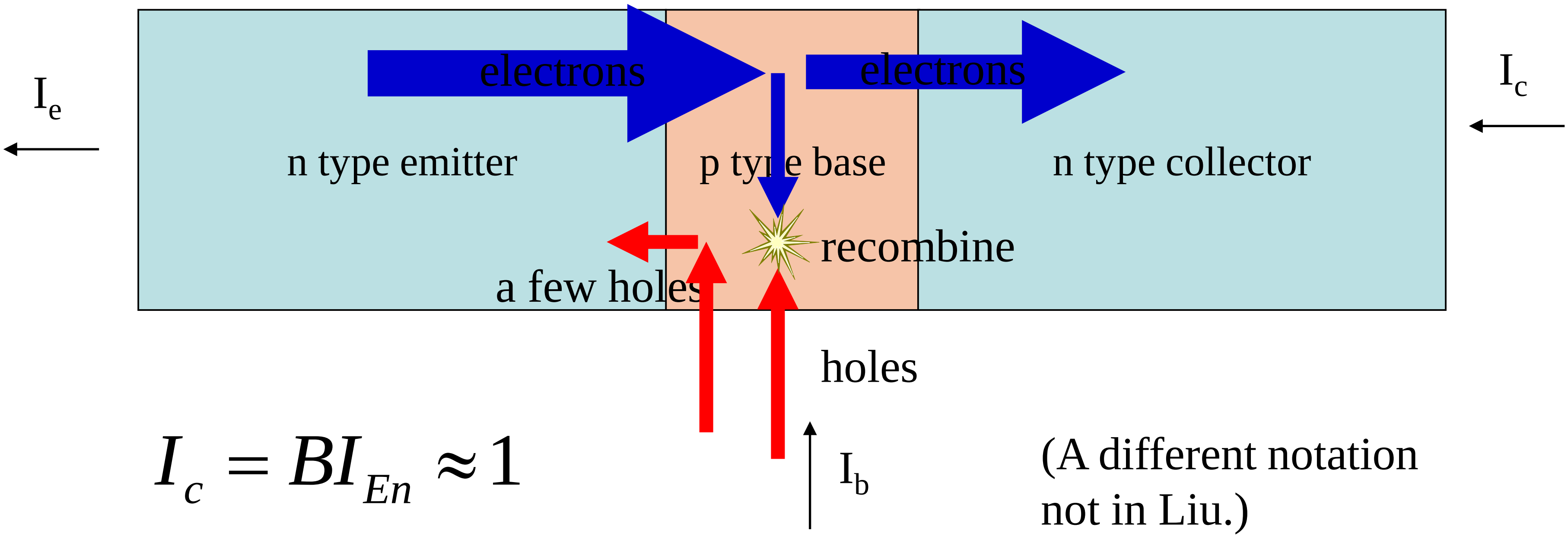


$$J_{B_p} = eD\frac{p_{n0}e^{eV_{BE}/kT}}{L_p}$$

$$J_{Brec.} = e\frac{Wn_{p0}e^{eV_{BE}/kT}}{2\tau_B} = eD\frac{n_{p0}e^{eV_{BE}/kT}}{X_B}$$

How to calculate:
Don’t use line for n(x) but tanh.
dn/dx em. – dn/dx coll = base curr.
Explain on board. Will be HW#3.

"Normal active" schematic



$$I_c = BI_{En} \approx 1$$

(A different notation not in Liu.)

$$\gamma \equiv \frac{I_{En}}{I_{Ep} + I_{En}} \approx 1$$

$$\frac{I_c}{I_E} = \frac{I_c}{I_{Ep} + I_{En}} = \frac{BI_{En}}{I_{Ep} + I_{En}} = \gamma B \equiv \alpha \approx 1$$

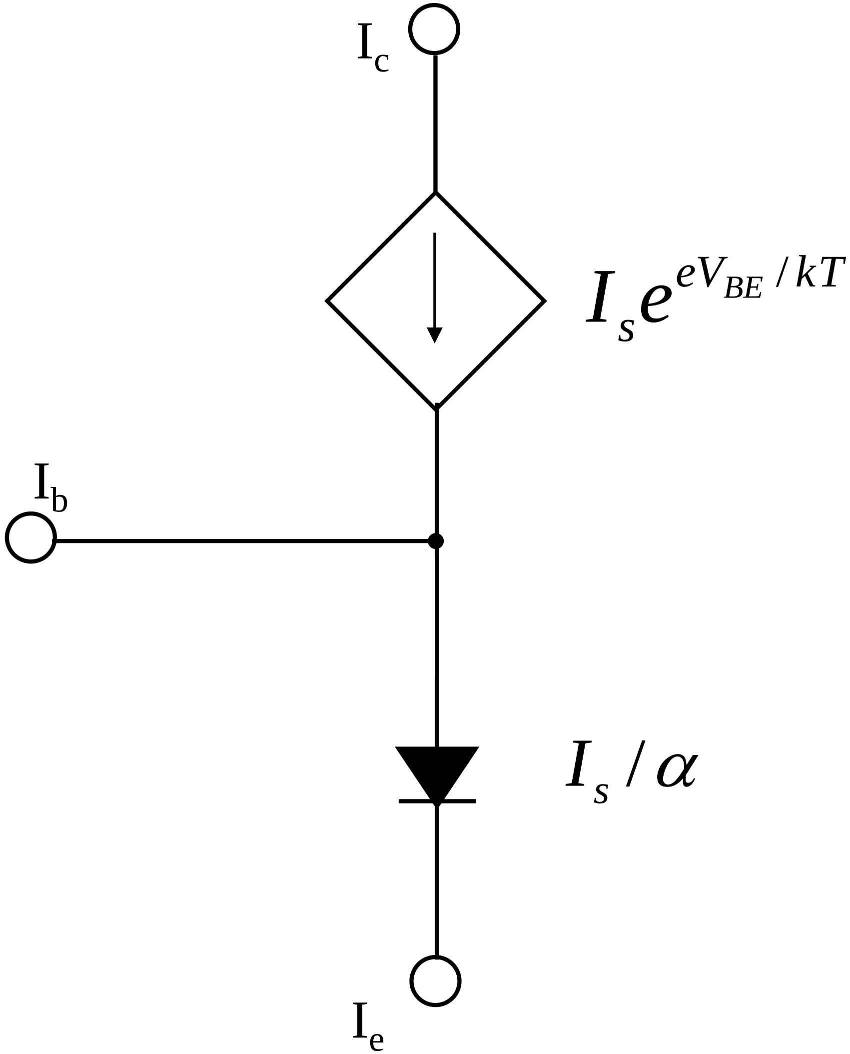
$$I_b = I_{Ep} + (1 - B) I_{En}$$

$$\frac{I_c}{I_b} = \frac{BI_{En}}{I_{Ep} + (1 - B) I_{En}} = \frac{\alpha}{1 - \alpha} \equiv \beta >> 1$$

Complications

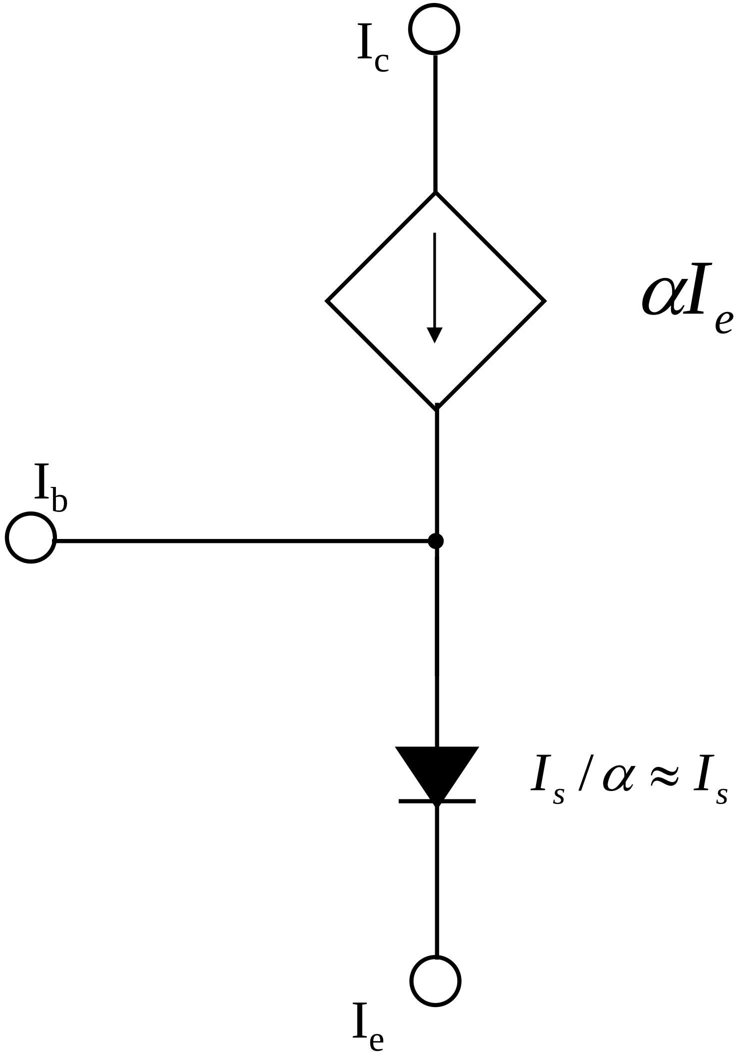
- High power
- Spreading resistance

Equivalent circuit 1



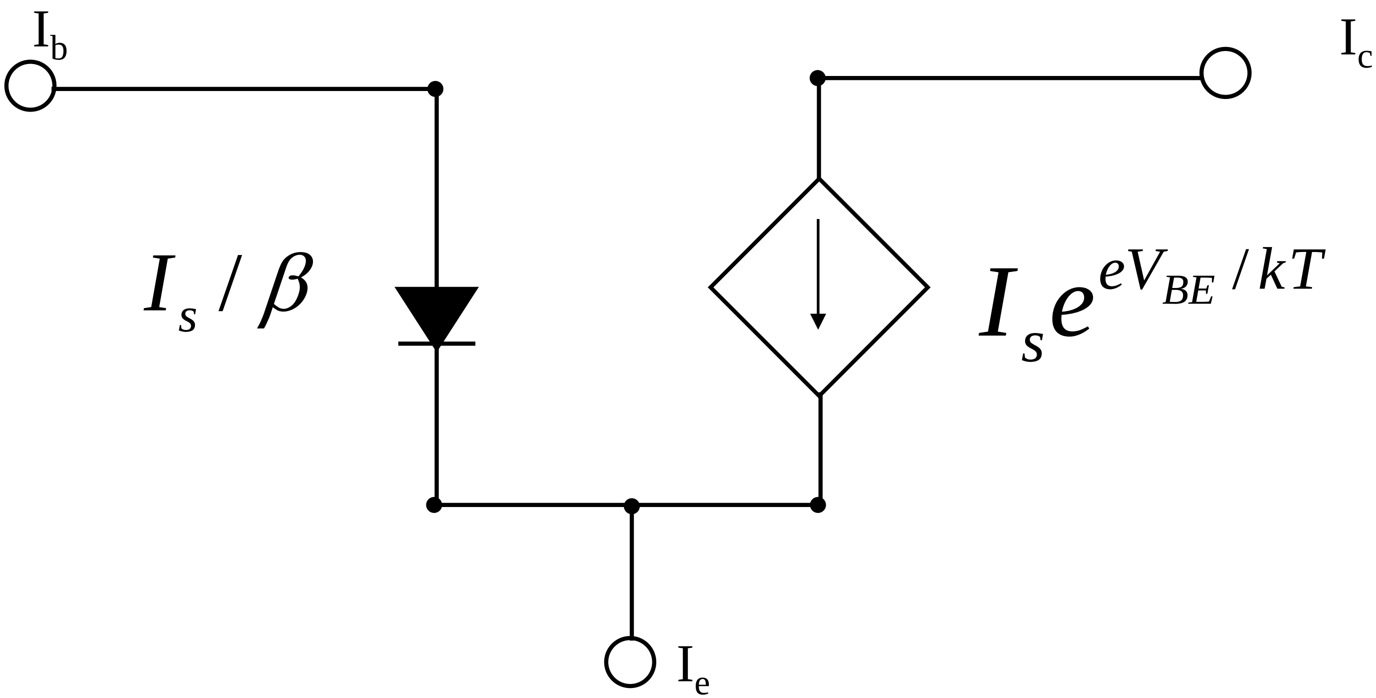
$$I_s \equiv \frac{AeDn_{po}}{X_B}$$

Equivalent circuit 2

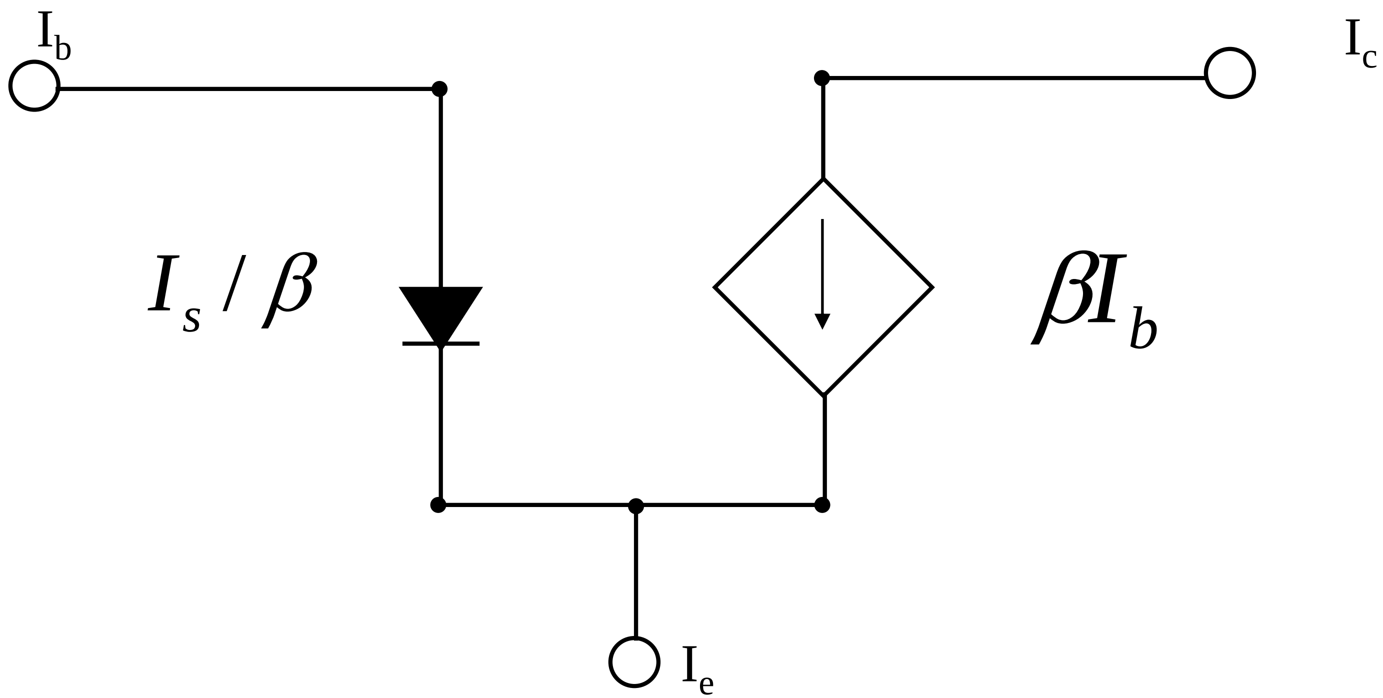


$$I_s \equiv \frac{AeDn_{po}}{X_B}$$

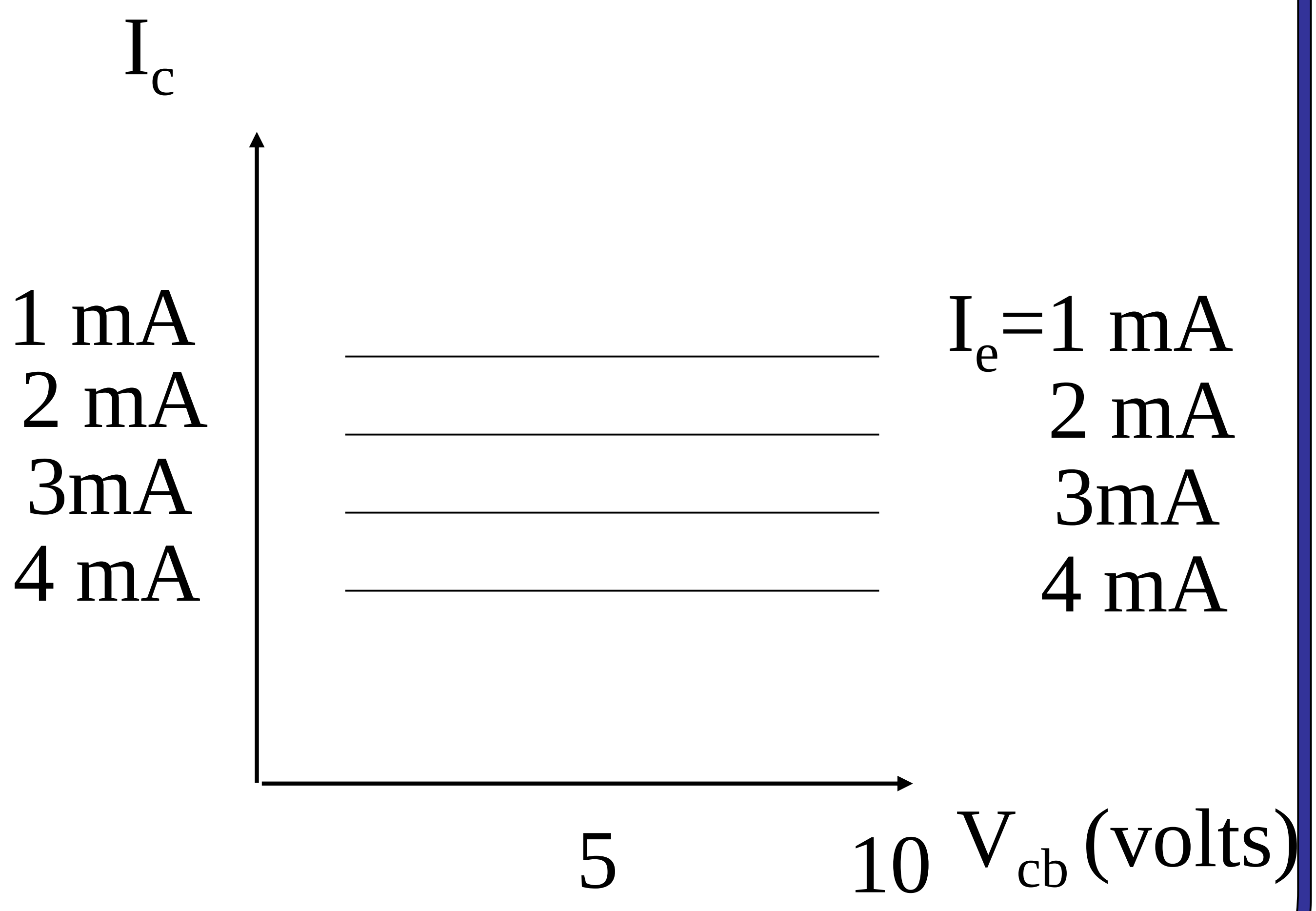
Equivalent circuit 3



Equivalent circuit 4



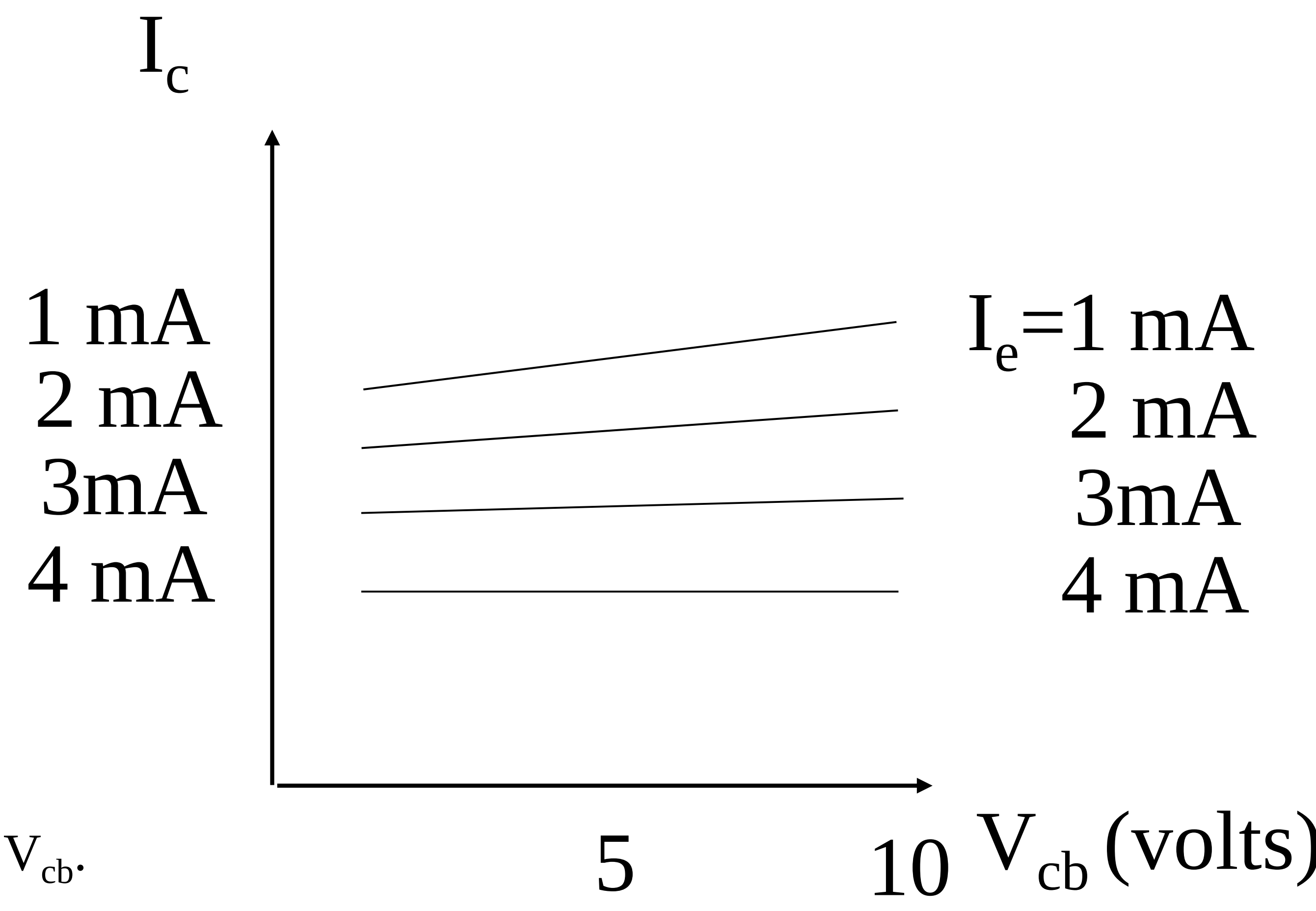
Early effect



Early effect

$$\frac{I_c}{I_b} \equiv \beta >> 1$$

$$\frac{I_c}{I_b} \approx \frac{\tau_n}{\tau_t}$$



W changes with V_{cb}.

Bipolar advantages

- Speed set by base width, which is easy to control
- Large area contributes to current, good for power

Bipolar dis-advantages

- Need base current at dc
- No easy complementary digital logic